

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	216	(tft or (thin near film near transistor)) and ((channel or (active adj layer) or (semiconductor adj layer)) near5 (portion or region) near5 (dope or doping or doped) near10 (threshold or (fixed near charge) or (charge near density)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:14
L2	3	(tft or (thin near film near transistor)) and ((channel or (active adj layer) or (semiconductor adj layer)) near5 (portion or region) near5 (dope or doping or doped) near10 (threshold or (fixed near charge) or (charge near density))) and ((channel or (active adj layer) or (semiconductor adj layer)) near10 ((tin adj oxide) or (zinc adj oxide) or (indium adj oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:16
L3	17	(tft or (thin near film near transistor)) and ((channel or (active adj layer) or (semiconductor adj layer)) near10 (portion or region) near10 (implant or implanting or implanted or implantation or dope or doping or doped) near10 (threshold or (fixed near charge) or (charge near density))) and ((channel or (active adj layer) or (semiconductor adj layer)) near10 ((tin adj oxide) or (zinc adj oxide) or (indium adj oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:24

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L53	69	I52 and ((channel or (active adj layer) or (semiconductor adj layer)) near10 ((zinc adj oxide) or (tin adj oxide) or (indium adj oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:37
L54	16	I52 and ((channel or (active adj layer) or (semiconductor adj layer)) near10 ((zinc adj oxide) or (tin adj oxide) or (indium adj oxide))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:34
L55	422	I52 and ((channel or (active adj layer) or (semiconductor adj layer)) near10 (dope or doping or doped or dopant or impurity or implant or implanting or implanted or implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:37
L56	46	I53 and ((channel or (active adj layer) or (semiconductor adj layer)) near10 (dope or doping or doped or dopant or impurity or implant or implanting or implanted or implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:42
L57	854	(channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:43
L58	37	I52 and (channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:46
L59	21	I52 and (channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation)) near10 (different or vary or varying or higher or lower or variable)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:47

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L60	5	I52 and (channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation)) near10 (different or vary or varying or higher or lower or variable) same ((fixed near charge) or (charge near density) or threshold)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:49
L61	15	I52 and (channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation)) near10 (different or vary or varying or higher or lower or variable) and (channel with ((fixed near charge) or (charge near density) or threshold))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:50
L62	16	I52 and (channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation)) near10 (different or differently or vary or varying or higher or lower or variable) and (channel with ((fixed near charge) or (charge near density) or threshold))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:51
L63	16	I52 and (channel near2 ((first or second or upper or lower or top or bottom) near (portion or region or layer or area)) near2 (dope or doping or doped or dopant or implant or implanting or implanted or implantation)) near10 (different or differently or vary or varying or higher or lower or variable) and ((channel or (active adj layer) or (semiconductor adj layer)) with ((fixed near charge) or (charge near density) or threshold))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/26 12:52